

251907US-2S DIV

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: :
SYOTARO ONO, ET AL. : GROUP UNIT:
SERIAL NO: NEW DIV. APPLN. :
FILED: HEREWITH : EXAMINER:
FOR: VERTICAL TYPE POWER MOSFET :
HAVING TRENCHED GATE
STRUCTURE

PRELIMINARY AMENDMENT

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Prior to initial examination on the merits, please amend the above-identified application as follows:

Amendments to the Specification begin on page 2 of this paper

Listing of the Claims begins on page 3 of this paper.

Remarks begin on page 5 of this paper.